## EE 435

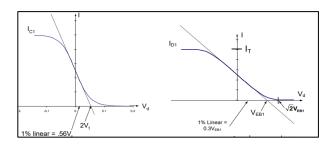
### Lecture 21

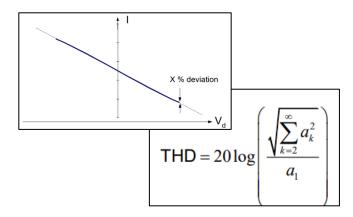
Linearity of Bipolar and MOS Differential Pairs Linearity of Common Source Amplifier Offset Voltages

### Executive Summary 03/03/23

#### Thank You Danny

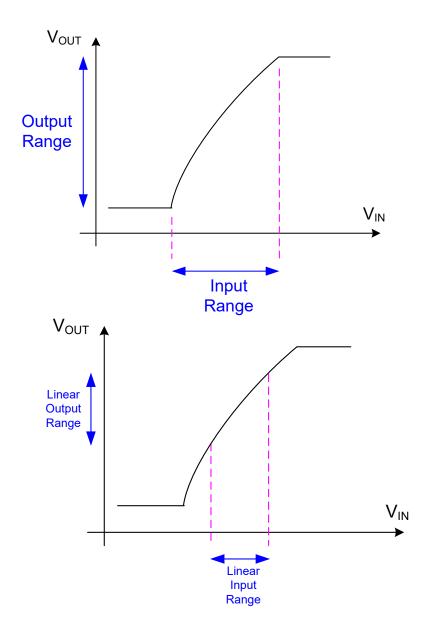
- Linearity in an amplifier is an important factor for spectral performance of feedback amplifiers and is of concern when used in OTA applications and differential input pairs.
- V<sub>EB</sub> affects linearity for a MOS differential pair.
- If we take the distance between the transfer characteristic of the line of best fit and divide it by the value of the line at that point, this results in point deviation.
- V<sub>t</sub> affects linearity for a BJT differential pair.
- For a bipolar differential transistor, designer has no control of intercept for BJT pair, and the slope/transition is steeper compared to MOS structure.
- Distortion in the differential pair can be used to characterize the linearity of the amplifier with sinusoidal differential excitation
- To minimize total harmonic distortion (THD), we want to have a large  $V_{EB}$ , a small  $V_M$  value, or both.





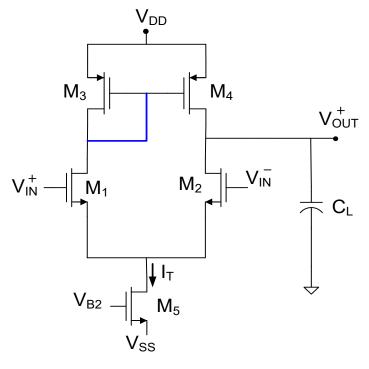
**Review from last lecture** 

Signal Swing and Linearity



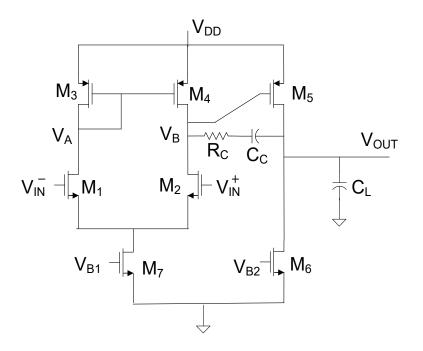
**Review from last lecture** 

# Linearity of Amplifiers



Single-Stage

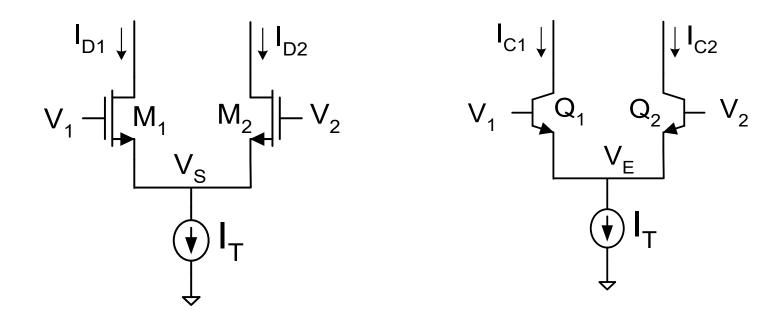
Linearity of differential pair of major concern



Two-Stage

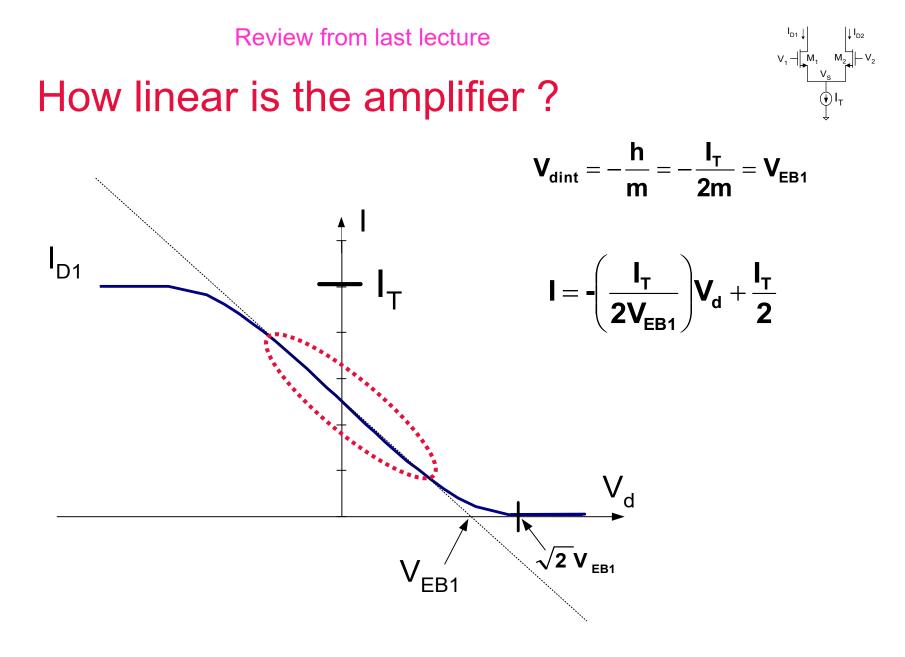
Linearity of common-source amplifier is of major concern (since signals so small at output of differential pair) **Review from last lecture** 

## **Differential Input Pairs**

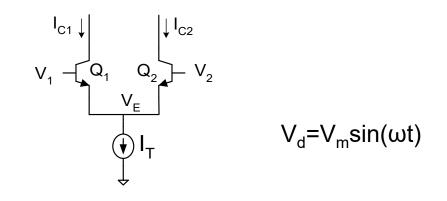


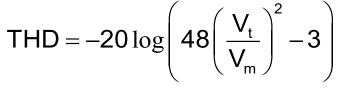
**MOS Differential Pair** 

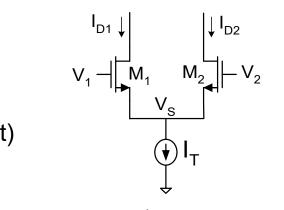
**Bipolar Differential Pair** 



## Comparison of Distortion in BJT and MOSFET Pairs



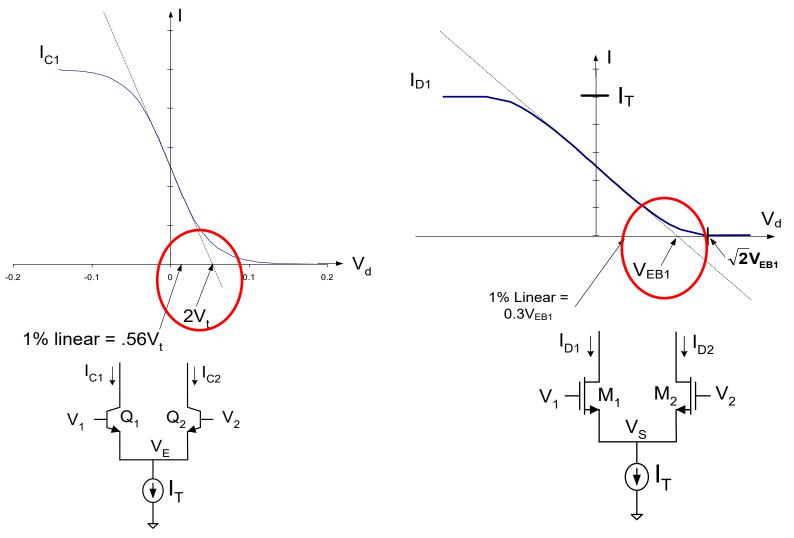






$V_m/V_t$	THD (dB)	$V_m/V_{EB1}$	THD (dB)	
2.5	-13.4049	2.5	-6.52672	
1	-33.0643	1	-29.248	
0.5	-45.5292	0.5	-41.9382	
0.25	-57.6732	0.25	-54.1344	
0.1	-73.6194	0.1	-70.0949	
0.05	-85.6647	0.05	-82.1422	
0.025	-97.7069	0.025	-94.1849	
0.01	-113.625	0.01	-110.103	

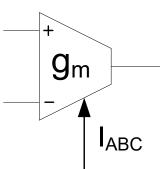
### Linearity and Signal Swing Comparison of Bipolar/MOS Differential Pair



Signal swing determined by V<sub>t</sub>

Signal swing determined by  $V_{EB}$ 

### Applications as a programmable OTA with IABC



The current-dependence of the  $g_m$  of the differential pair (single transistor) is often used to program the transconductance of an OTA with the tail bias current  $I_{ABC}$ 



$$g_m = \sqrt{I_{ABC}} \sqrt{\mu C_{OX}} \frac{W}{L}$$

Two decade change in current for every decade change in  $g_m$ 

$$g_m = uC_{OX} \frac{W}{L} V_{EB}$$

$$g_m = \frac{I_{ABC}}{2V_t}$$

BJT

One decade change in current for every decade change in  $g_m$ 

#### What change in signal swing if programmed with $I_{ABC}$ ?

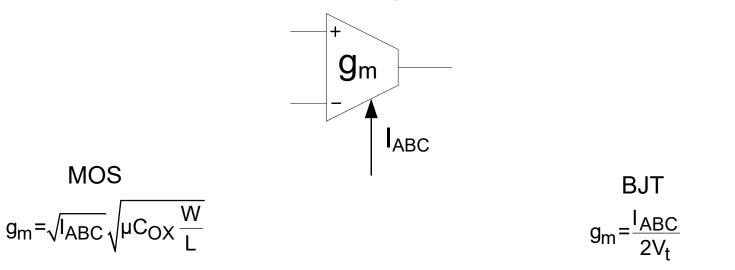
One decade decrease in signal swing for every decade decrease in  $g_{\rm m}$ 

No change in signal swing when g<sub>m</sub> Is changed

Limited g<sub>m</sub> adjustment possibility

Large g<sub>m</sub> adjustment possible

### Applications as a programmable OTA with I<sub>ABC</sub>



One decade decrease in signal swing for every decade decrease in  $g_m$ 

No change in signal swing when  $\ensuremath{g_{m}}$  Is changed

Assume a MOS transconductor has an acceptable signal swing (as determined by linearity) with  $V_{EB}$ =1V (maybe p-p signal swing is  $V_{EB}$ )

What would be the acceptable signal swing (with the same linearity) if  $g_m$  were tuned by one decade with  $I_{ABC}$ ?

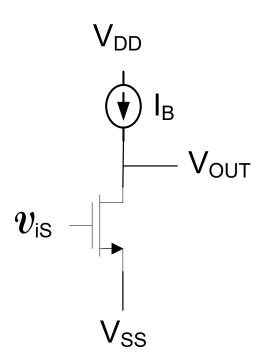
$$V_{\text{EB1}} = \sqrt{I_{\text{DQ}}} \sqrt{\frac{2L}{\mu C_{\text{OX}} W}} \qquad V_{\text{EB2}} = \sqrt{\frac{I_{\text{DQ}}}{100}} \sqrt{\frac{2L}{\mu C_{\text{OX}} W}} = \frac{1}{10} \sqrt{I_{\text{DQ}}} \sqrt{\frac{2L}{\mu C_{\text{OX}} W}} = \frac{V_{\text{EB1}}}{10}$$

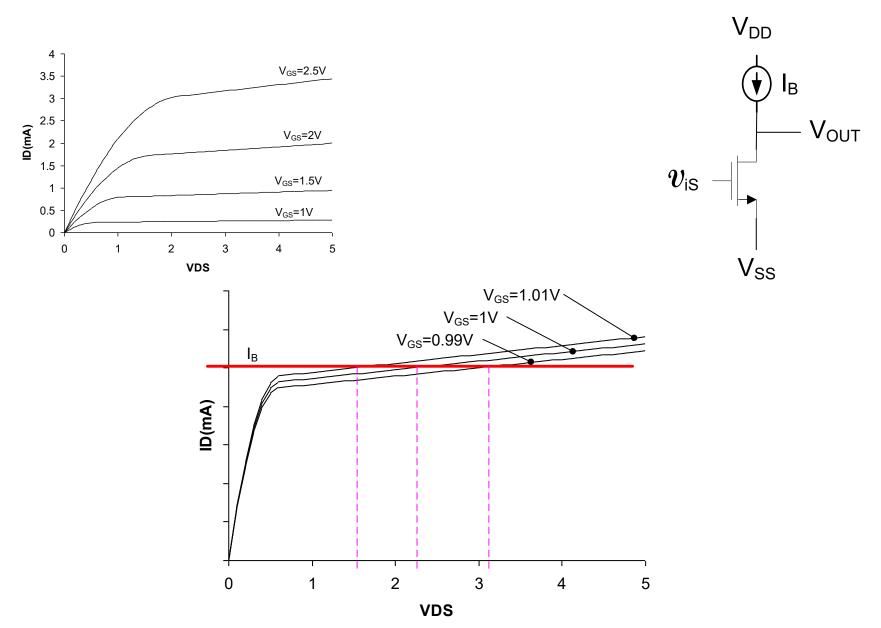
Signal swing would be reduced by a factor of 10

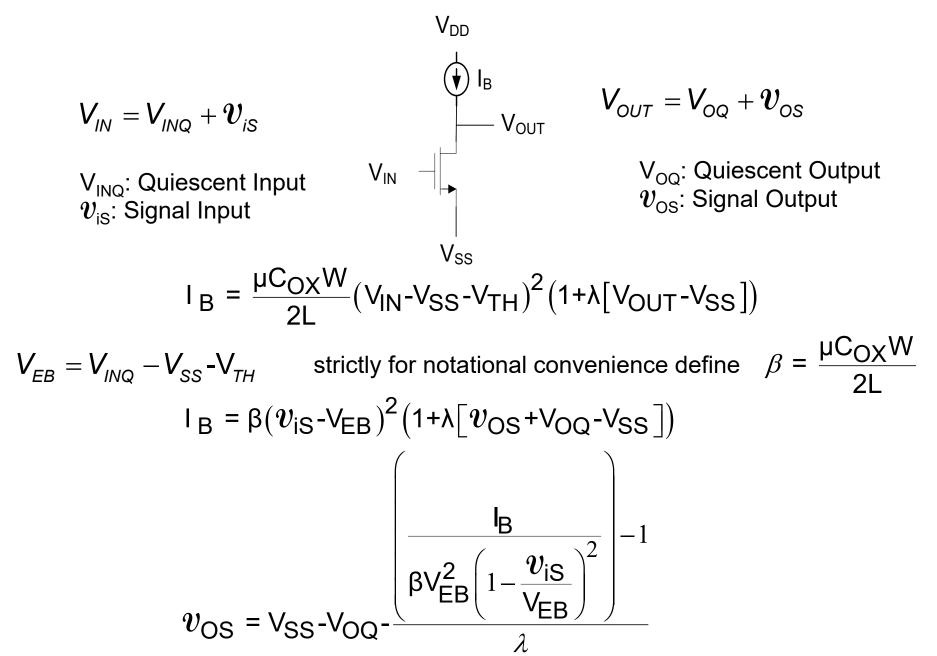
## Signal Swing and Linearity Summary

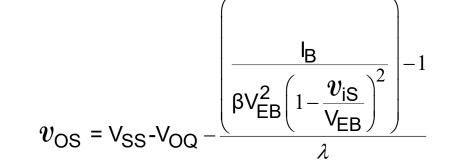
- Signal swing of MOSFET can be rather large if  $V_{\rm EB}$  is large but this limits gain
- Signal swing of MOSFET degrades significantly if  $V_{\rm EB}$  is changed for fixed W/L
- Bipolar swing is very small but independent of g<sub>m</sub>
- Multiple-decade adjustment of bipolar g<sub>m</sub> is practical
- Even though bipolar input swing is small, since gain is often very large, this small swing does usually not limit performance in feedback applications

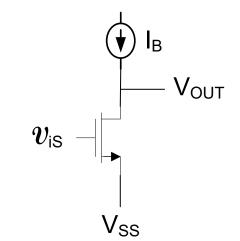
For convenience, will consider situation where current source biasing  ${\sf I}_{\sf B}$  is ideal

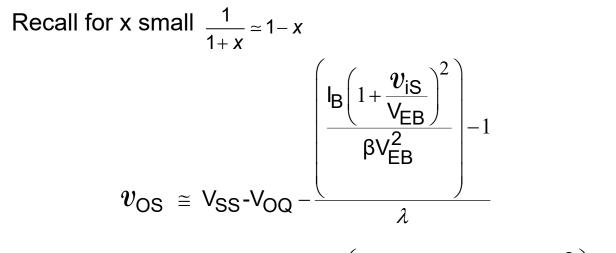










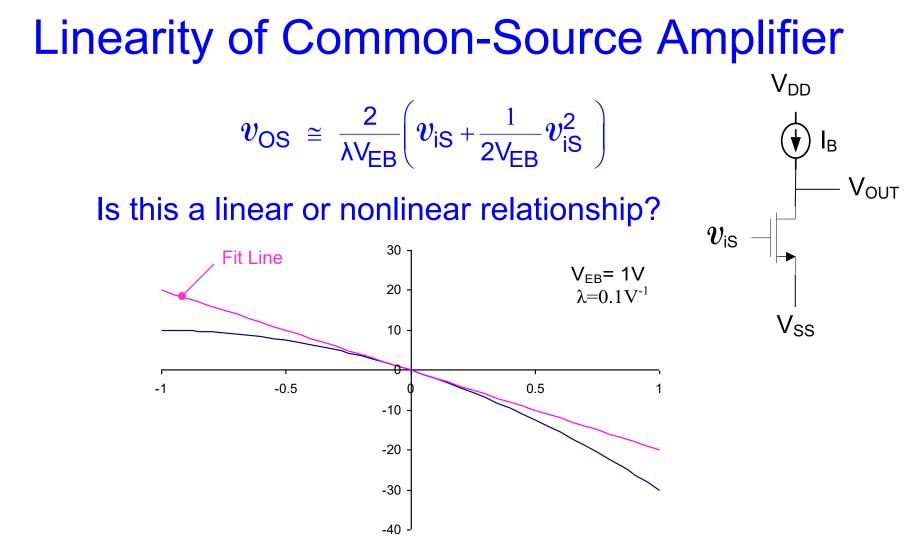


$$\boldsymbol{v}_{\text{OS}} \cong V_{\text{SS}} - V_{\text{OQ}} - \frac{l_{\text{B}}}{\lambda \beta V_{\text{EB}}^2} \left( 1 + 2\frac{\boldsymbol{v}_{\text{iS}}}{V_{\text{EB}}} + \left(\frac{\boldsymbol{v}_{\text{iS}}}{V_{\text{EB}}}\right)^2 \right) - \frac{1}{\lambda}$$
$$\boldsymbol{v}_{\text{OS}} \cong \left[ V_{\text{SS}} - V_{\text{OQ}} - \frac{1}{\lambda} \left(\frac{l_{\text{B}}}{\beta V_{\text{EB}}^2} + 1\right) \right] - \frac{l_{\text{B}}}{\lambda \beta V_{\text{EB}}^2} \left( 2\frac{\boldsymbol{v}_{\text{iS}}}{V_{\text{EB}}} + \left(\frac{\boldsymbol{v}_{\text{iS}}}{V_{\text{EB}}}\right)^2 \right)$$

Thus

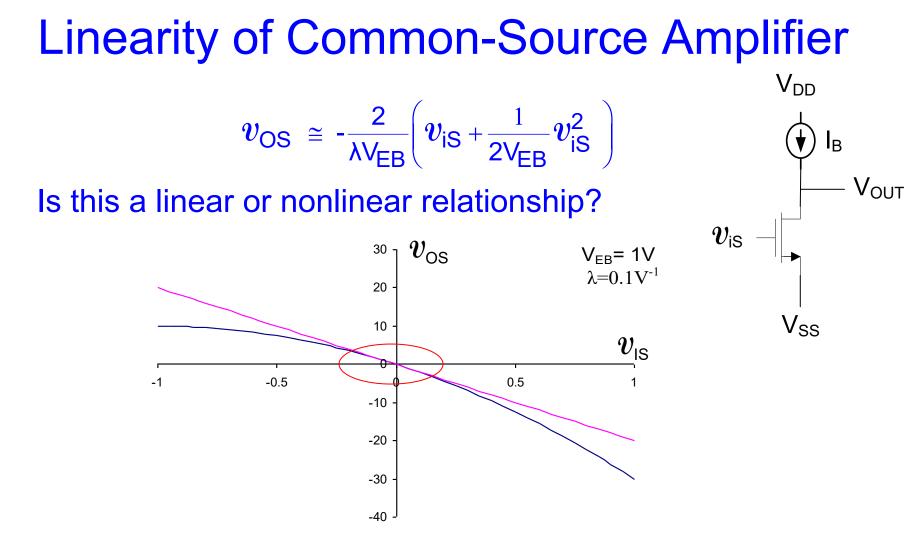
$$\boldsymbol{v}_{\text{OS}} \cong -\left(2\frac{\boldsymbol{v}_{\text{iS}}}{\lambda V_{\text{EB}}} + \frac{1}{\lambda} \left(\frac{\boldsymbol{v}_{\text{iS}}}{V_{\text{EB}}}\right)^2\right)$$
$$\boldsymbol{v}_{\text{OS}} \cong -\frac{2}{\lambda V_{\text{EB}}} \left(\boldsymbol{v}_{\text{iS}} + \frac{1}{2V_{\text{EB}}} \boldsymbol{v}_{\text{iS}}^2\right)$$

Is this a linear or nonlinear relationship?



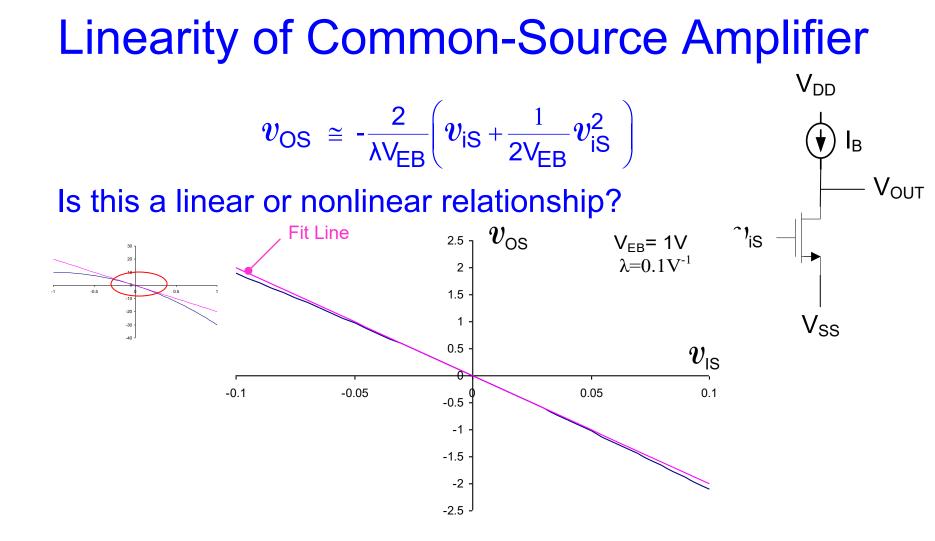
when  $v_{iS} = -V_{EB}$  (the minimum value of  $v_{iS}$  to maintain saturation operation) the error in  $V_{OS}$  will be  $V_{EB}/2$  which is -50% !

#### Is this a linear or nonlinear relationship?



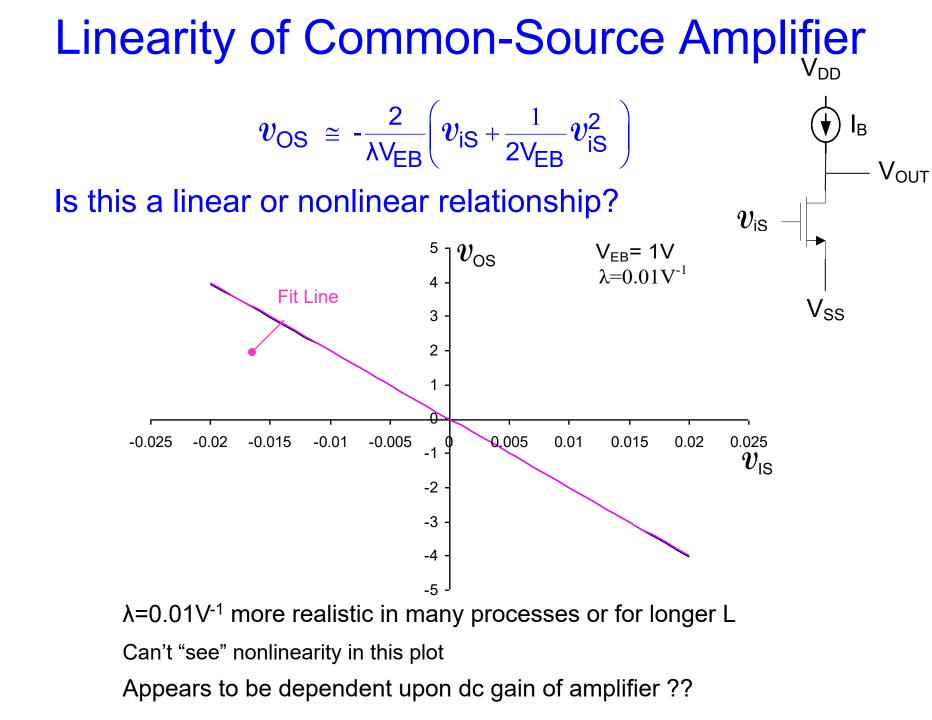
Note this is a reasonably high gain amplifier and could be larger for smaller  $V_{EB}$ 

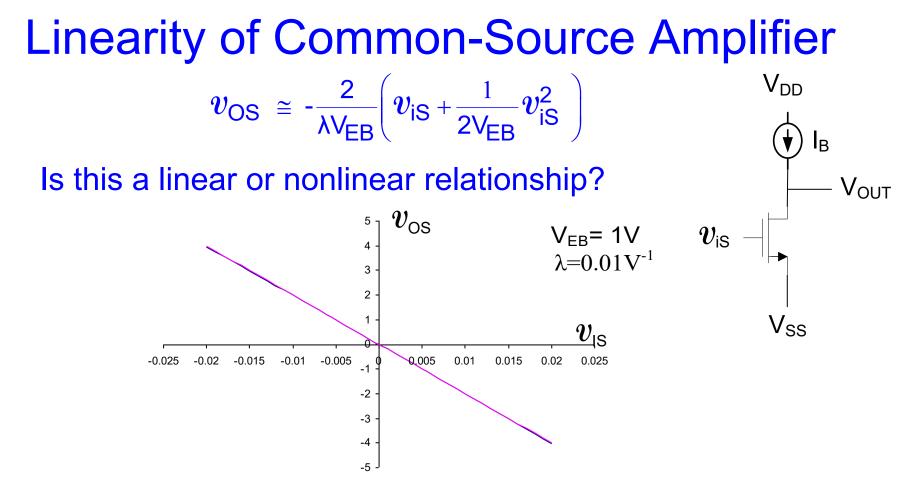
Over what output voltage range are we interested?



Linearity is reasonably good over practical input range

Practical input range is much less than  $V_{EB}$ 

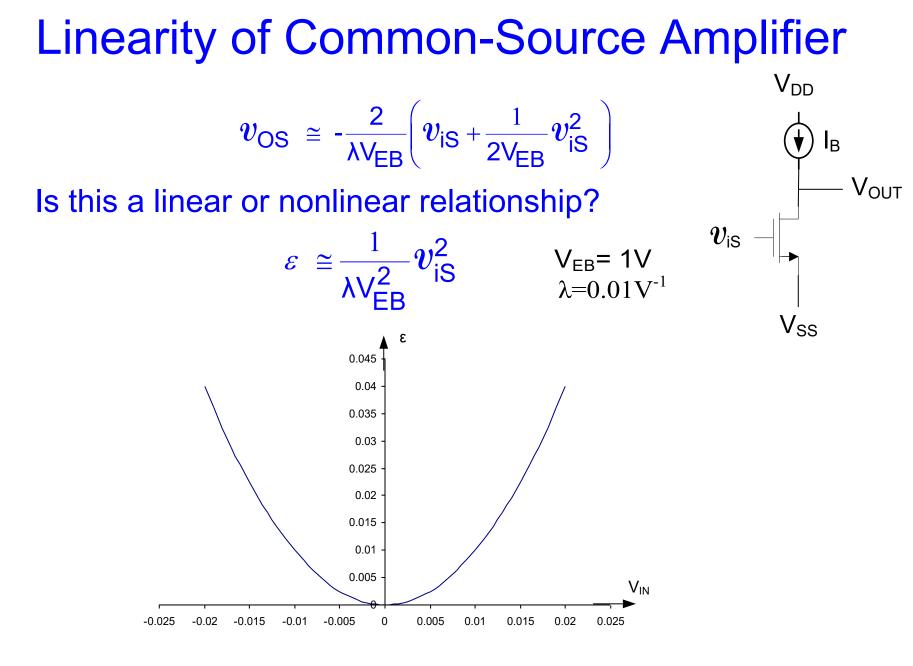




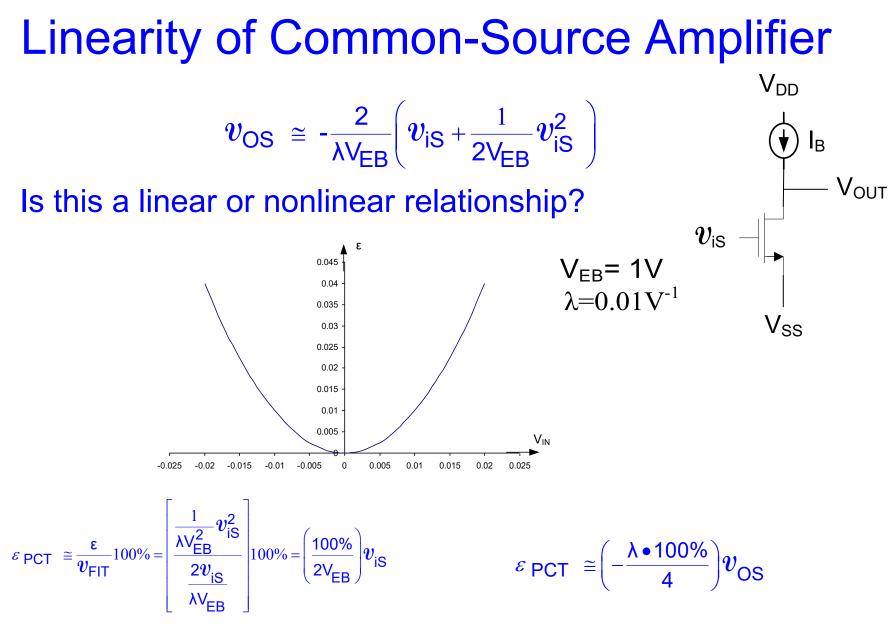
Will look at difference between output and ideal output as defined by fit lie

$$v_{\text{FIT}} \cong -\frac{2}{\lambda V_{\text{EB}}} v_{\text{iS}}$$
  
 $\varepsilon \equiv v_{\text{FIT}} - v_{\text{oS}}$   
 $\varepsilon \cong \frac{1}{\lambda V_{\text{EB}}^2} v_{\text{iS}}^2$ 

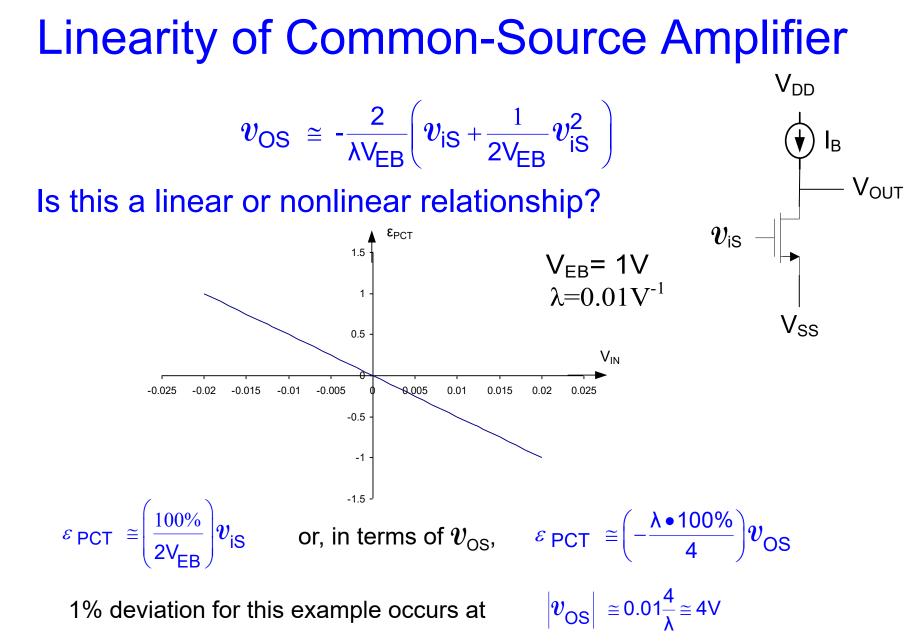
Appears to be highly dependent upon dc gain of amplifier ??



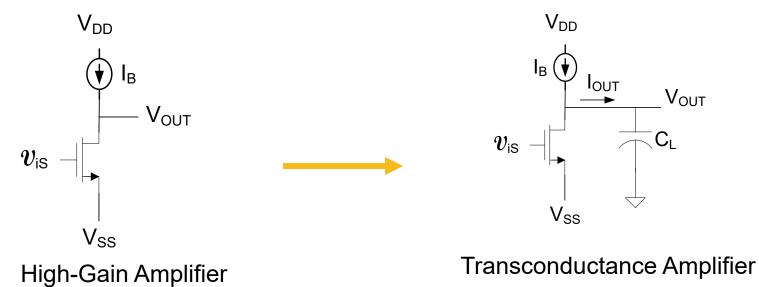
Appears to be highly dependent upon dc gain of amplifier ??



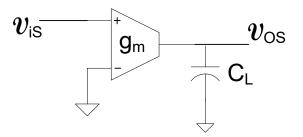
Appears to be highly dependent upon dc gain of amplifier ?? Relative error in output independent of gain of amplifier !



In spite of square-law nonlinearity in MOSFET, linearity of CS amplifier is quite good provided MOSFET remains in saturation region !!

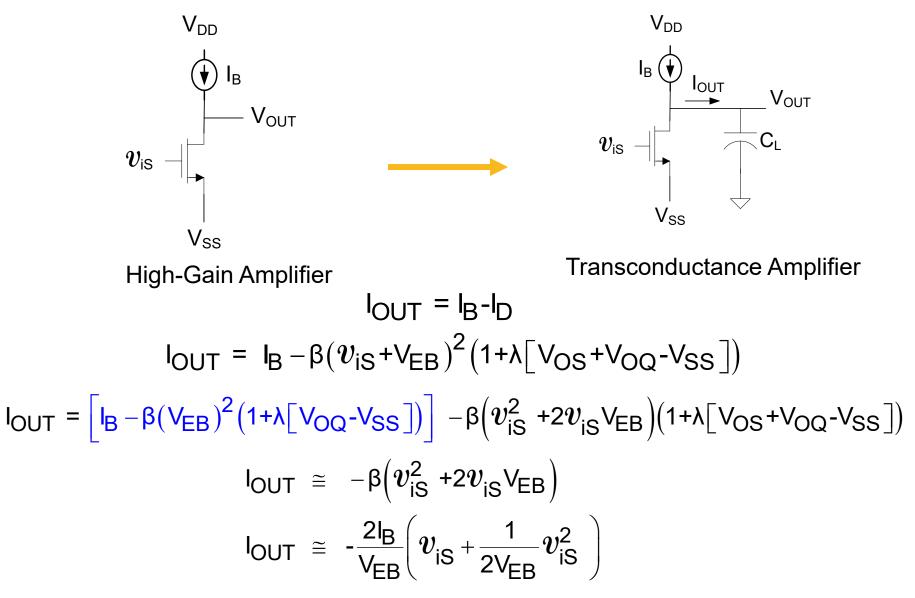


The transconductance amplifier driving a load C<sub>L</sub> is performing as an integrator

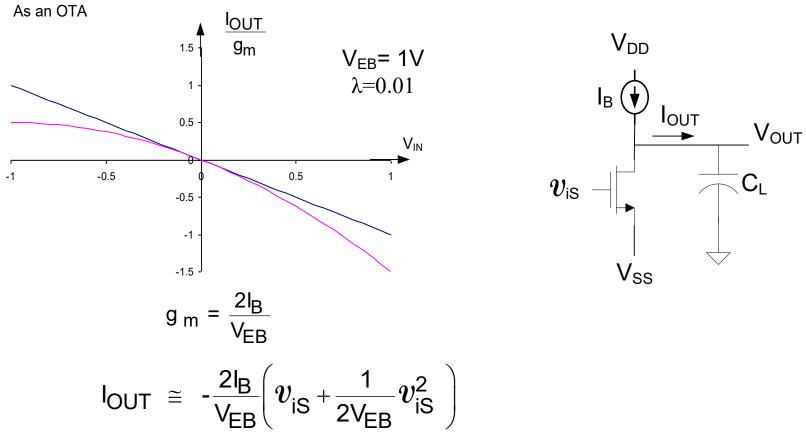


Integrators often used in filters where at frequencies of most interest  $|v_{\rm OS}|$  is comparable to  $|v_{\rm iS}|$ 

### Is this common-source amplifier linear or nonlinear?

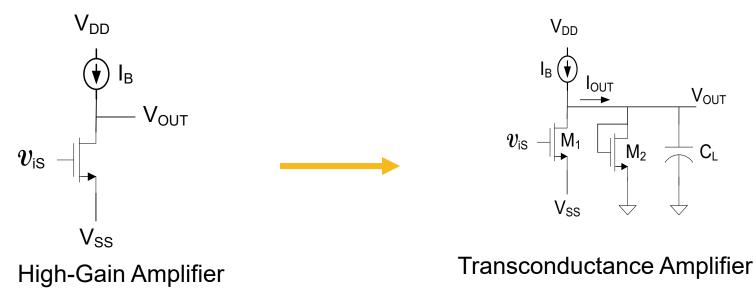


Is this a linear or nonlinear relationship?



#### Is this a linear or nonlinear relationship?

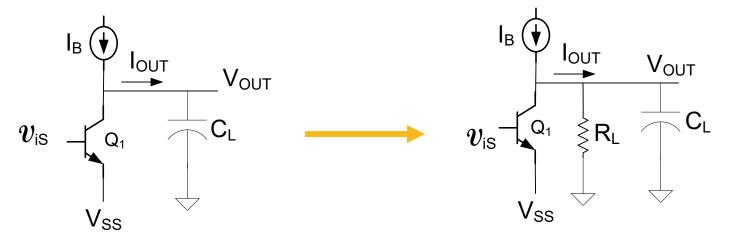
At  $v_{IS}$ =-V<sub>EB</sub>, the error in I<sub>OUT</sub> will be -50% !



#### Is this common-source amplifier linear?

- Reasonably linear if used in high-gain applications and  $V_{EB}$  is large (e.g. if  $A_V = g_m/g_o = 2/((\lambda V_{EB}) = 100$  and Vo = 1V, Vin=10mV)
- Highly nonlinear when used in low-gain applications though linearity dependent upon  ${\rm g}_{\rm m}$

## Linearity of Common-Emitter Amplifier



**High-Gain Amplifier** 

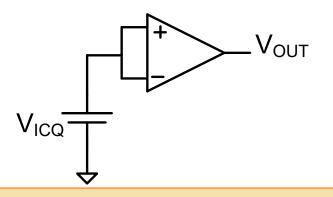
Transconductance Amplifier

#### Is this common-emitter amplifier linear?

- Very linear if used in high-gain applications (e.g. if A<sub>V</sub>=g<sub>m</sub>/g<sub>0</sub>=V<sub>AF</sub>/V<sub>t</sub>=4000 and V<sub>o</sub>=1V, V<sub>in</sub>=250uV)
- Highly nonlinear when used in low-gain applications but not dependent upon  $g_{\rm m}$
- Bipolar OTAs (e.g. current mirror op amp) can operate over multiple decades of gain with low-level signals but no degradation with gain

Two types of offset voltage:

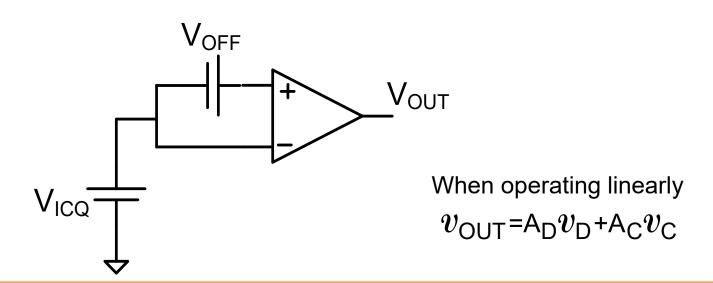
- Systematic Offset Voltage
- Random Offset Voltage



Definition: The output offset voltage is the difference between the desired output and the actual output when  $V_{id}$ =0 and  $V_{ic}$  is the quiescent common-mode input voltage.

### VOUTOFF = VOUT - VOUTDES

Note:  $V_{OUTOFF}$  is dependent upon  $V_{ICQ}$  although this dependence is usually quite weak and often not specified



Definition: The input-referred offset voltage is the differential dc input voltage that must be applied to obtain the desired output when  $V_{ic}$  is the quiescent common-mode input voltage.

 $V_{OFF}$  is usually related to the output offset voltage by the expression

$$V_{OFF} = \frac{V_{OUTOFF}}{A_D}$$

 $V_{OFF}$  is dependent upon  $V_{ICQ}$  although this dependence is usually quite weak and often not specified

V<sub>OFF</sub> almost always large enough to force open-loop op amp out of linear mode for good op amps

### Note: Our definition differs from that of most others

#### From Wikipedia March 12, 2022

The **input offset voltage** ( $V_{os}$ ) is a parameter defining the differential DC voltage required between the inputs of an amplifier, especially an operational amplifier (op-amp), to make the output zero (for voltage amplifiers, 0 volts with respect to ground or between differential outputs, depending on the output type).<sup>[1]</sup>

#### From Analog Devices MT-037 Tutorial

Ideally, if both inputs of an op amp are at exactly the same voltage, then the output should be at zero volts. In practice, a small differential voltage must be applied to the inputs to force the output to zero. This is known as the input offset voltage,  $V_{OS}$ 

Offset Voltage: The differential voltage which must be applied to the input of an op amp to produce zero output.

### Note: Our definition differs from that of most others

From Texas Instruments Application Note: SLOA059 – March 2001

#### Input Offset Voltage Defined

The input offset voltage is defined as the voltage that must be applied between the two input terminals of the op amp to obtain zero volts at the output. Ideally the output of the op amp should be at zero volts when the inputs are grounded.

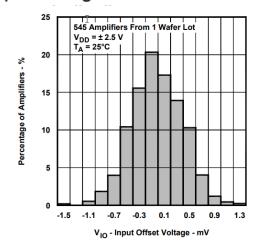


Figure 3. Distribution of  $V_{IO}$  for the TLV2721

Implicit in the definition of  $V_{\rm OS}$  by most others is that the desired output voltage of an op amp is 0v when the differential input is 0V

From Analog Devices MT-037 Tutorial

#### Ranges:

Chopper Stabilized Op Amps:	<1µV
General Purpose Precision Op Amps:	50-500μV
Best Bipolar Op Amps:	10-25µV
Best JFET Input Op Amps:	100-1,000μV
High Speed Op Amps:	100-2,000μV
Untrimmed CMOS Op Amps:	5,000-50,000µV
● DigiTrim <sup>™</sup> CMOS Op Amps:	<100µV-1,000µV

#### Figure 1: Typical Op Amp Input Offset Voltage

These ranges probably are applicable to catalog op amps

From Analog Devices MT-037 Tutorial

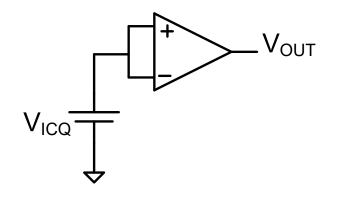
#### **INPUT OFFSET VOLTAGE DRIFT AND AGING EFFECTS**

Input offset voltage varies with temperature, and its temperature coefficient is known as *TCVos*, or more commonly, *drift*. Offset drift is affected by offset adjustments to the op amp, but when the offset voltage of a bipolar input op amp has been minimized, the drift may be as low as  $0.1 \,\mu\text{V/}^\circ\text{C}$  (typical value for <u>OP177F</u>). More typical drift values for a range of general purpose precision op amps lie in the range 1-10  $\mu\text{V/}^\circ\text{C}$ . Most op amps have a specified value of TCVos, but some, instead, have a second value of maximum Vos that is guaranteed over the operating temperature range. Such a specification is less useful, because there is no guarantee that TCVos is constant or monotonic.

The offset voltage also changes as time passes, or *ages*. Aging is generally specified in  $\mu$ V/month or  $\mu$ V/1000 hours, but this can be misleading. Since aging is a "drunkard's walk" phenomenon, it is proportional to the *square root* of the elapsed time. An aging rate of 1  $\mu$ V/1000 hour therefore becomes about 3  $\mu$ V/year (not 9  $\mu$ V/year).

Two types of offset voltage:

- Systematic Offset Voltage
- Random Offset Voltage



After fabrication it is impossible (difficult) to distinguish between the systematic offset and the random offset in any individual op amp

Measurements of offset voltages for a large number of devices will provide mechanism for identifying systematic offset and statistical characteristics of the random offset voltage

### Systematic Offset Voltage

Offset voltage that is present if all device and model parameters assume their nominal value

Easy to simulate the systematic offset voltage

Almost always the designer's responsibility to make systematic offset voltage very small

Generally easy to make the systematic offset voltage small

### Random Offset Voltage

- Due to random variations in process parameters and device dimensions
- Random offset is actually a random variable at the design level but deterministic after fabrication in any specific device
- Distribution naturally nearly Gaussian (could be un-naturally manipulated)

Has zero mean

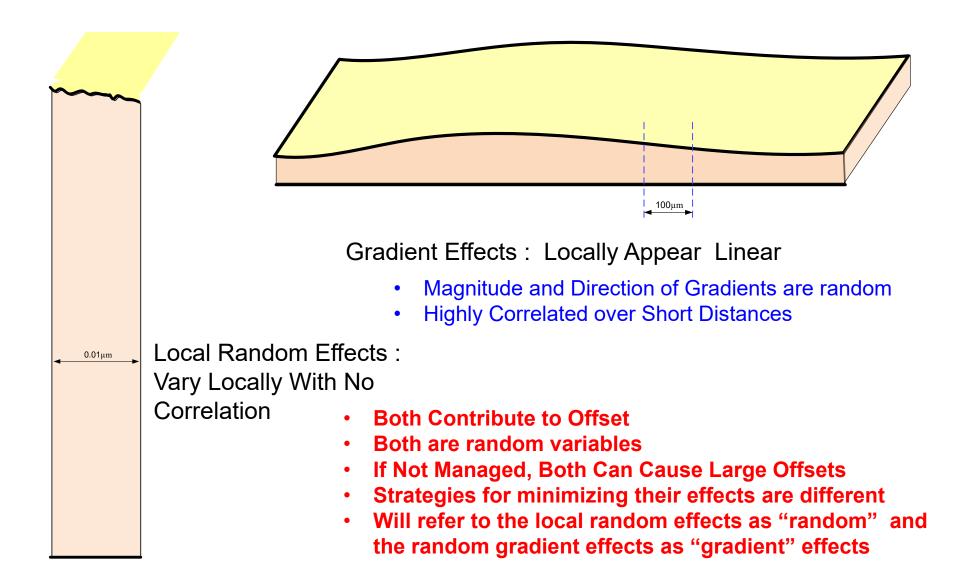
Characterized by its standard deviation or variance

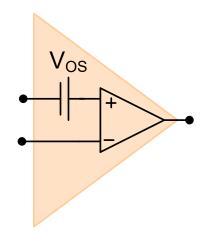
Often strongly layout dependent

Due to both local random variations and correlated gradient effects

- Will consider both effects separately
- Gradient effects usually dominate if not managed
- Good methods exist for driving gradient effects to small levels

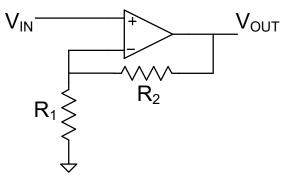
## Gradient and Local Random Effect



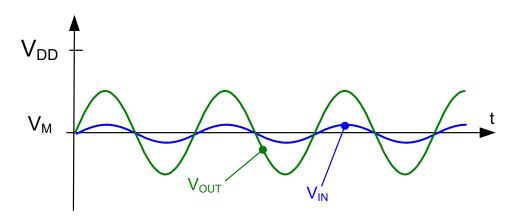


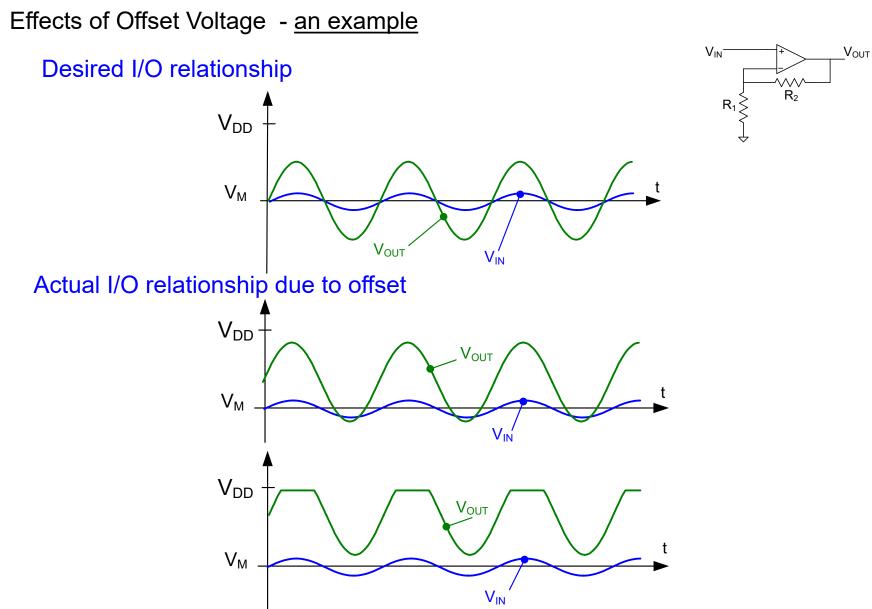
Can be modeled as a dc voltage source in series with the input

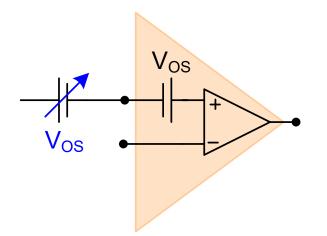
Effects of Offset Voltage - an example



Desired I/O relationship







Effects can be reduced or eliminated by adding equal amplitude opposite DC signal (many ways to do this)

Widely used in offset-critical applications

Comes at considerable effort and expense for low offset

#### Prefer to have designer make $V_{OS}$ small in the first place

# Effects of Offset Voltage

- Deviations in performance will change from one instantiation to another due to the random component of the offset
- Particularly problematic in high-gain circuits
- A major problem in many other applications
- Not of concern in many applications as well



# Stay Safe and Stay Healthy !

## End of Lecture 21